

NTE1680
Integrated Circuit
High Speed, 6 Diode Array, Common Anode

Description:

The NTE1680 is a common anode monolithic array of high speed switching diodes in a 7-Lead SIP type package.

Features:

- High Speed Switching Time: $t_{rr} = 4.0\text{ns}$ Typ.
- Low Capacitance: $C_t = 5.0\text{pf}$ TYP.
- Small Size Enables High Density Mounting

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Peak Reverse Voltage, V_{RM}	75V
Reverse Voltage, V_R	50V
Peak Forward Surge Current (Per Unit), $I_{F\text{surge}}$	1A
Peak Forward Current (1 μs , Per Unit), I_{FM}	200mA
Average Rectified Current (Per Unit), I_O	100mA
Power Dissipation (Per Package), P_D	300mW
Operating Junction Temperature, T_J	+125 $^\circ\text{C}$
Storage Temperature Range, T_{stg}	-55 $^\circ$ to + 125 $^\circ\text{C}$

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage Drop	V_F	$I_F = 30\text{mA}$	–	0.8	1.0	V
Reverse Current	I_R	$V_R = 30\text{V}$	–	0.005	0.1	μA
Terminal Capacitance (Per Unit)	C_t	$V_R = 0, f = 1.0\text{MHz}$	–	5.0	8.0	pF
Reverse Recovery Time	t_{rr}		–	4.0	8.0	ns

Pin Connection Diagram
(Front View)

